



MM 980nm 25Gbps VCSEL (Bottom Emission)

QZV25MM0980B101

QZV25MM0980B102

QZV25MM0980B103

fight the world

CONTENTS

- Descriptions
 Features
 Applications
- Absolute Maximum Ratings
 Recommended Operating Conditions &
 Electro-Optic Characteristics
- Chip Outer Dimensions
 Chip Layout
 RoHS Compliance
- Ordering Information



Description

The QuantumZ - QZV25MM0980BX0X is multimode 25Gbps VCSEL with wavelength 980nm device has low electrical parasitics and proven high reliability. That has bottom side ohmic contacts with Signal-Ground (SG) configurations. The device is available in singlet (1x1) or array configurations (1x4) and are compatible with wire-bonding and flip-chip bonding.

Features

- 980nm multimode emission
- High reliability & data rates from DC to 25Gbps
- High humidity robustness compliant with GR-468
- Low threshold, operating voltage & electrical parasitic
- Available as single chip & 4 channel array
- Available application for COB & flip chip processes
- Dual top contact configuration with common cathode electrodes
- Halogen & RoHS compliant

Applications

- Smart cables & consumer applications & Automotive
- Single channel & parallel fiber optical communication links

Absolute Maximum Ratings

Parameter	Rating	Unit	
Max. operating power	6	mW	
Max. operating current	12	mA	
VCSEL reverse voltage	5	V	
Operating temperature	0 to 105	°C	
Storage temperature	-40 to 125	°C	
Mounting temperature (max. 10sec)	260	°C	

Recommended Operating Conditions

& Electro-Optic Characteristics

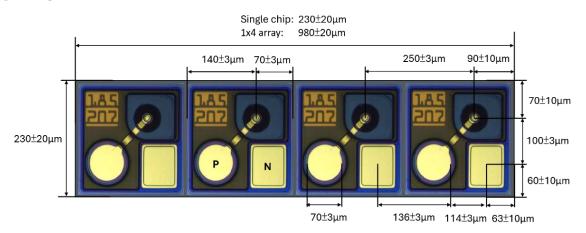
Parameter	Conditions	Ratings		Unit			
Parameter	Symbol	Conditions		Тур.	Max.	Unit	
Threshold current		T=25°C		0.5	0.7	- mA	
	I _{th}	T=105°C		0.8	1.0	IIIA	
Slope efficiency	η	Iop = 6.0mA, T=25°C		0.5		W/A	
Optical output power	В	lop = 6.0mA, T=25°C	2.5	3.0		\//	
	Pout	lop = 6.0mA, T=105°C	2.0	2.5		mW	
Forward voltage	Vf	Iop=6.0mA, T=25°C	1.8	1.9	2.1	V	
Differential resistance	R _d	lop=6mA, T=25°C~105°C		80	90	Ω	
Emission wavelength	λ	lop = 6.0mA, T=25°C~105°C	970	980	990	nm	
Spectral width, RMS	Δλ	lop=6mA, T=25°C~105°C		0.8		nm	
Wavelength Shift	dλ/dT	T = 25 °C~105 °C		0.07		nm/°C	
Modulation bandwidth	f _{3dB}	Iop=6mA, T=25°C	15	18		GHz	
		Iop=9mA, T=105°C	14	16			
Beam divergence	Θ	lop = 6.0mA, Full width 1/e2		25	30	Deg	



Chip Outer Dimensions

Parameter	Min.	Тур.	Max.
Die length	225	250	275
Die width	225	250	275
Die height	125	150	175

Chip Layout



P: p-contact (anode)

N: n-contact (common cathode)

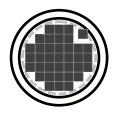
RoHS Compliance

QuantumZ insists, via continuous improvement in technology and experiences, to utilize non-hazardous materials for manufacturing green products that are in compliance with the regulation as well as customers' GP demands. The relevant evidence of RoHS compliance is held as part of our controlled documentation for each of our compliant products.

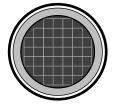
Ordering Information

Product code	Data Rate	Description	Shipment Package
QZV25MM0980B101	25Gbps	Single VCSEL chip	Diced wafer on metal lead frame (1)
QZV25MM0980B401	25Gbps	1x4 VCSEL array	Diced wafer on metal lead frame (1)
QZV25MM0980B102	25Gbps	Single VCSEL chip	Grip ring (2)
QZV25MM0980B402	25Gbps	1x4 VCSEL array	Grip ring (2)
QZV25MM0980B103	25Gbps	Single VCSEL chip	Gel-Pak (3)
QZV25MM0980B403	25Gbps	1x4 VCSEL array	Gel-Pak (3)

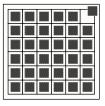
- (1) Full diced 4" wafer on UV tape on metal lead frame Ø 230mm, electronic wafer map provided (standard high volume)
- (2) Known Good Dies on UV tape on grip ring Ø 150mm (medium volume)
- (3) Known Good Dies in 2" Gel-Pak (low volume)



Diced wafer on UV tape on metal lead



Grip ring



Gel-Pak